

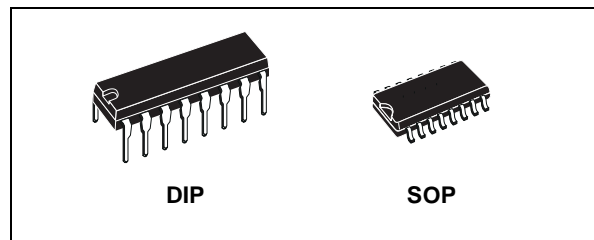


4-BIT MAGNITUDE COMPARATOR

- EXPANSION TO 8, 12, 16...4 N BITS BY CASCADING UNIT
- MEDIUM SPEED OPERATION : COMPARES TWO 4-BIT WORDS IN 180ns (Typ.) at 10V
- STANDARDIZED SYMMETRICAL OUTPUT CHARACTERISTICS
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT
 $I_l = 100\text{nA (MAX) AT } V_{DD} = 18\text{V } T_A = 25^\circ\text{C}$
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"

DESCRIPTION

HCF4585B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. HCF4585B is a 4-bit magnitude comparator designed for use in computer and logic applications that require the comparison of two 4-bit words. This logic circuit determines whether one 4-bit word (Binary or BCD) is "less than", "equal to" or "greater than" a second 4-bit word.

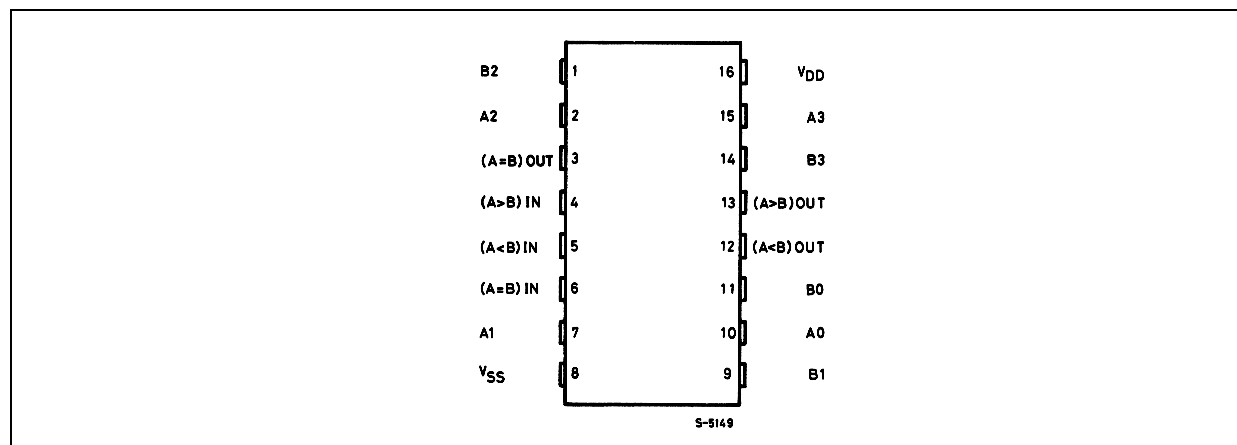


ORDER CODES

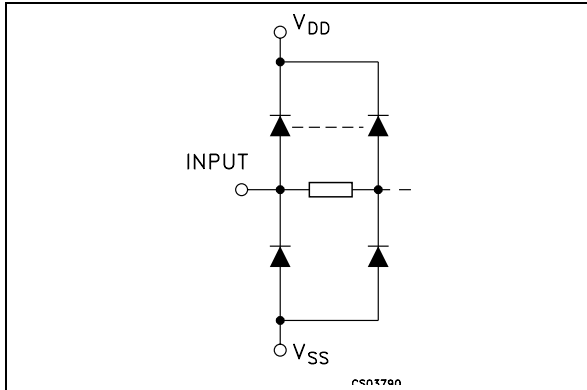
PACKAGE	TUBE	T & R
DIP	HCF4585BEY	
SOP	HCF4585BM1	HCF4585M013TR

HCF4585B has eight comparing inputs (A3, B3 through A0, B0), three outputs (A<B, A=B, A>B) and three cascading inputs (A<B, A=B, A>B) that permit system designers to expand the comparator function to 8, 12, 16...4N bits. When a single HCF4585B is used, the cascading inputs are connected as follows: (A<B) = low, (A=B) = high, (A>B) = high. Cascading these units for comparison of more than 4 bits is accomplished as shown in Typical application.

PIN CONNECTION



IINPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

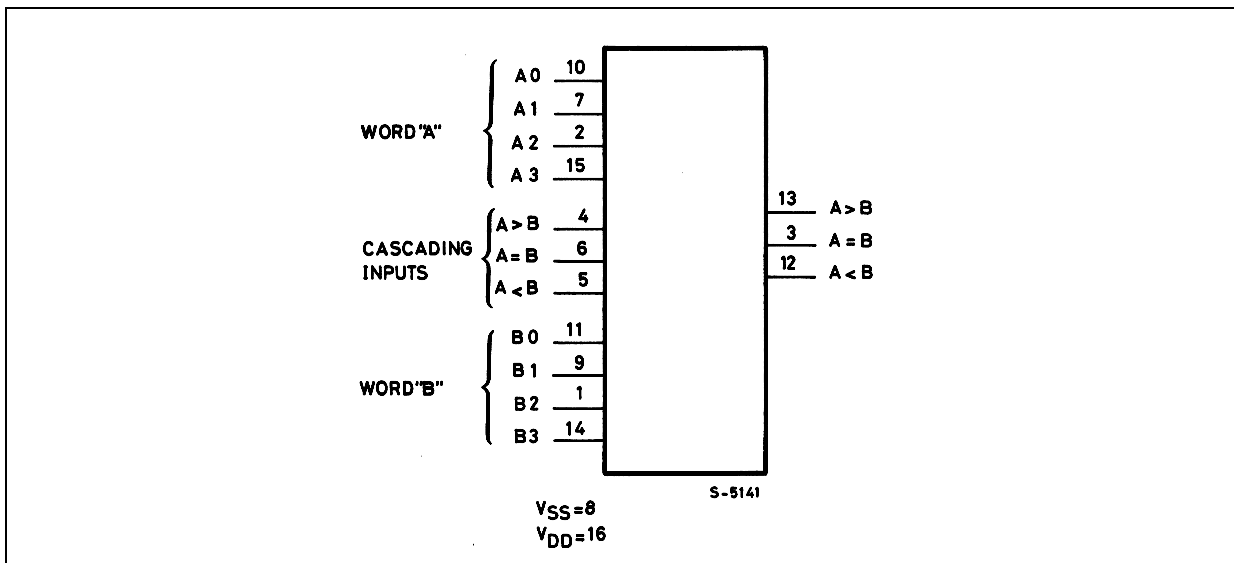
PIN No	SYMBOL	NAME AND FUNCTION
10, 7, 2, 15	A0 to A3	Word A Inputs
11, 9, 1, 14	B0 to B3	Word B Inputs
13, 3, 12	A>B, A=B, A<B	Outputs
4, 6, 5	A>B, A=B, A<B	Cascading Inputs
8	V _{SS}	Negative Supply Voltage
16	V _{DD}	Positive Supply Voltage

TRUTH TABLE

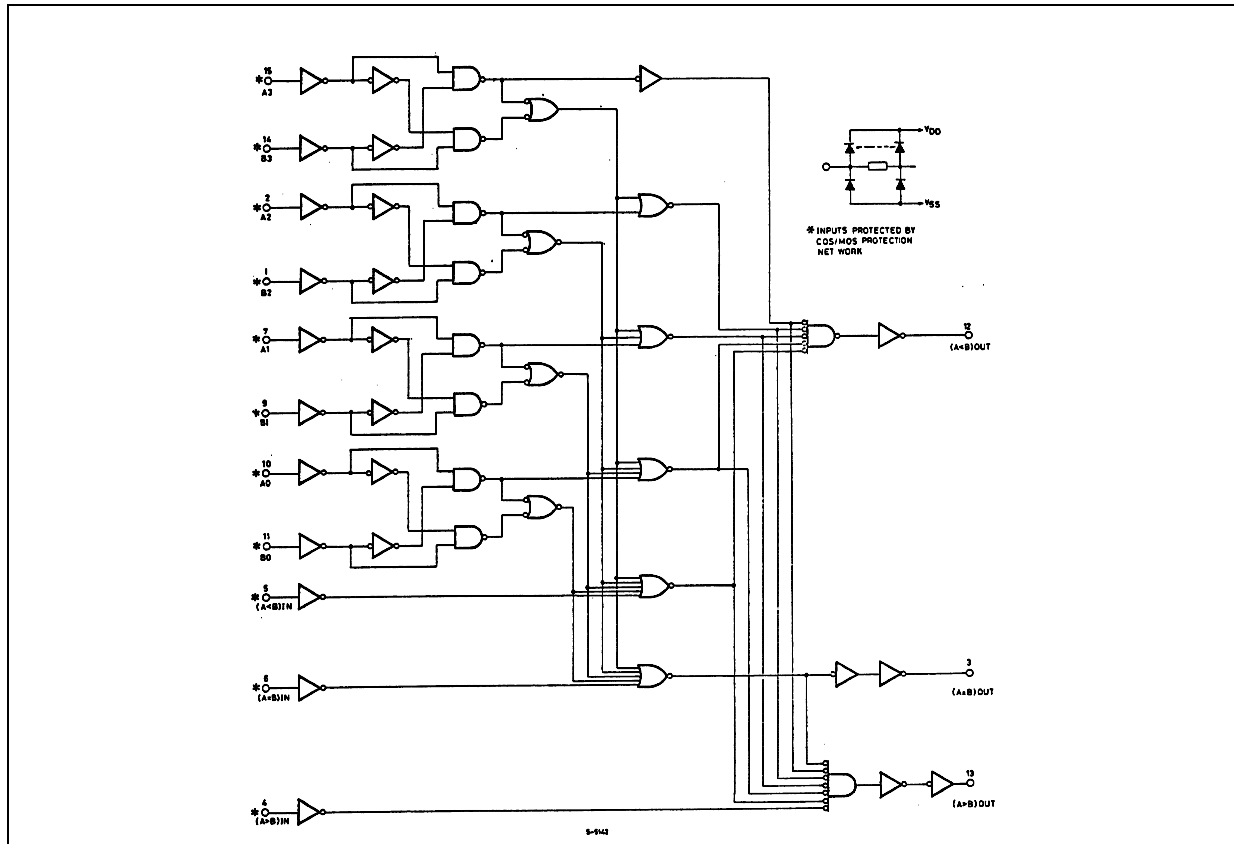
INPUTS							OUTPUTS		
COMPARING				CASCADING					
A3, B3	A2, B2	A1, B1	A0, B0	A<B	A=B	A>B	A<B	A=B	A>B
A3 > B3	X	X	X	X	X	H	L	L	H
A3 = B3	A2 > B2	X	X	X	X	H	L	L	H
A3 = B3	A2 = B2	A1 > B1	X	X	X	H	L	L	H
A3 = B3	A2 = B2	A1 = B1	A0 > B0	X	X	H	L	L	H
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	L	H	L	L	H
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	H	X	L	H	L
A3 = B3	A2 = B2	A1 = B1	A0 = B0	H	L	X	H	L	L
A3 = B3	A2 = B2	A1 = B1	A0 < B0	X	X	X	H	L	L
A3 = B3	A2 < B2	X	X	X	X	X	H	L	L
A3 < B3	X	X	X	X	X	X	H	L	L

X : Don't Care

FUNCTIONAL DIAGRAM



LOGIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	-0.5 to +22	V
V_I	DC Input Voltage	-0.5 to $V_{DD} + 0.5$	V
I_I	DC Input Current	± 10	mA
P_D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T_{op}	Operating Temperature	-55 to +125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-65 to +150	$^{\circ}\text{C}$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{DD}	Supply Voltage	3 to 20	V
V_I	Input Voltage	0 to V_{DD}	V
T_{op}	Operating Temperature	-55 to 125	$^{\circ}\text{C}$

DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value						Unit	
		V _I (V)	V _O (V)	I _{ol} (μA)	V _{DD} (V)	T _A = 25°C			-40 to 85°C		-55 to 125°C		
						Min.	Typ.	Max.	Min.	Max.	Min.		Max.
I _L	Quiescent Current	0/5			5		0.04	5		150		150	μA
		0/10			10		0.04	10		300		300	
		0/15			15		0.04	20		600		600	
		0/20			20		0.08	100		3000		3000	
V _{OH}	High Level Output Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
V _{OL}	Low Level Output Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
V _{IH}	High Level Input Voltage		0.5/4.5	<1	5	3.5			3.5		3.5		V
			1/9	<1	10	7			7		7		
			1.5/13.5	<1	15	11			11		11		
V _{IL}	Low Level Input Voltage		4.5/0.5	<1	5			1.5		1.5		1.5	V
			9/1	<1	10			3		3		3	
			13.5/1.5	<1	15			4		4		4	
I _{OH}	Output Drive Current	0/5	2.5	<1	5	-1.36	-3.2		-1.1		-1.1		mA
		0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I _{OL}	Output Sink Current	0/5	0.4	<1	5	0.44	1		0.36		0.36		mA
		0/10	0.5	<1	10	1.1	2.6		0.9		0.9		
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I _I	Input Leakage Current	0/18	Any Input		18		±10 ⁻⁵	±0.1		±1		±1	μA
C _I	Input Capacitance		Any Input				5	7.5					pF

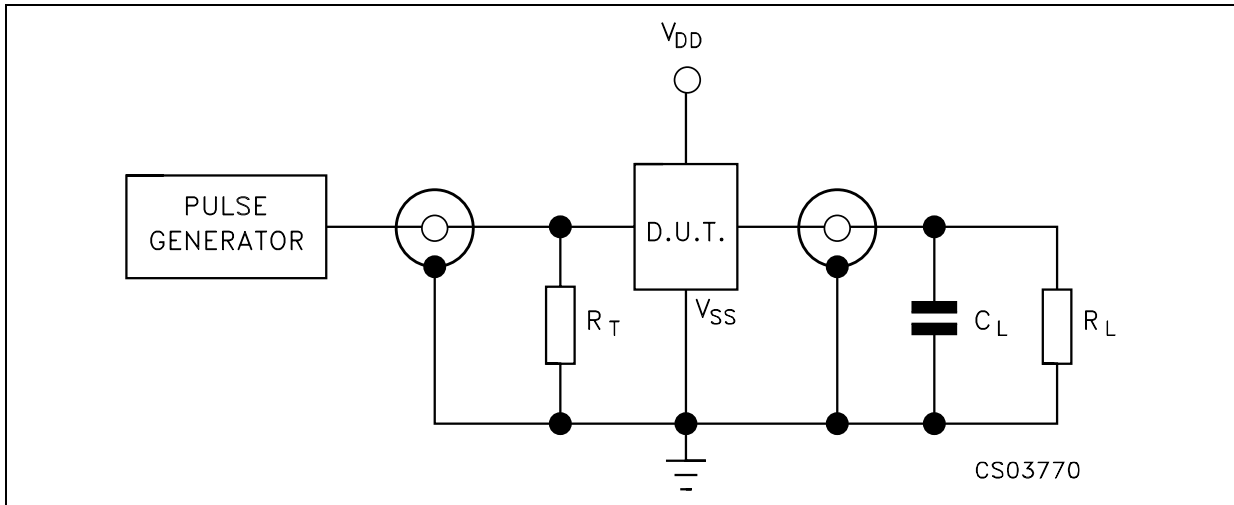
The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD}=5V, 2V min. with V_{DD}=10V, 2.5V min. with V_{DD}=15V

DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200KΩ, t_r = t_f = 20 ns)

Symbol	Parameter	Test Condition			Value (*)			Unit
		V _{DD} (V)			Min.	Typ.	Max.	
t _{PHL} t _{PLH}	Propagation Delay Time	5	Comparing Inputs to Outputs			300	600	ns
		10				125	250	
		15				80	160	
t _{PHL} t _{PLH}	Propagation Delay Time	5	Cascading Inputs to Outputs			200	400	ns
		10				80	160	
		15				60	120	
t _{THL} t _{TLH}	Transition Time	5				100	200	ns
		10				50	100	
		15				40	80	

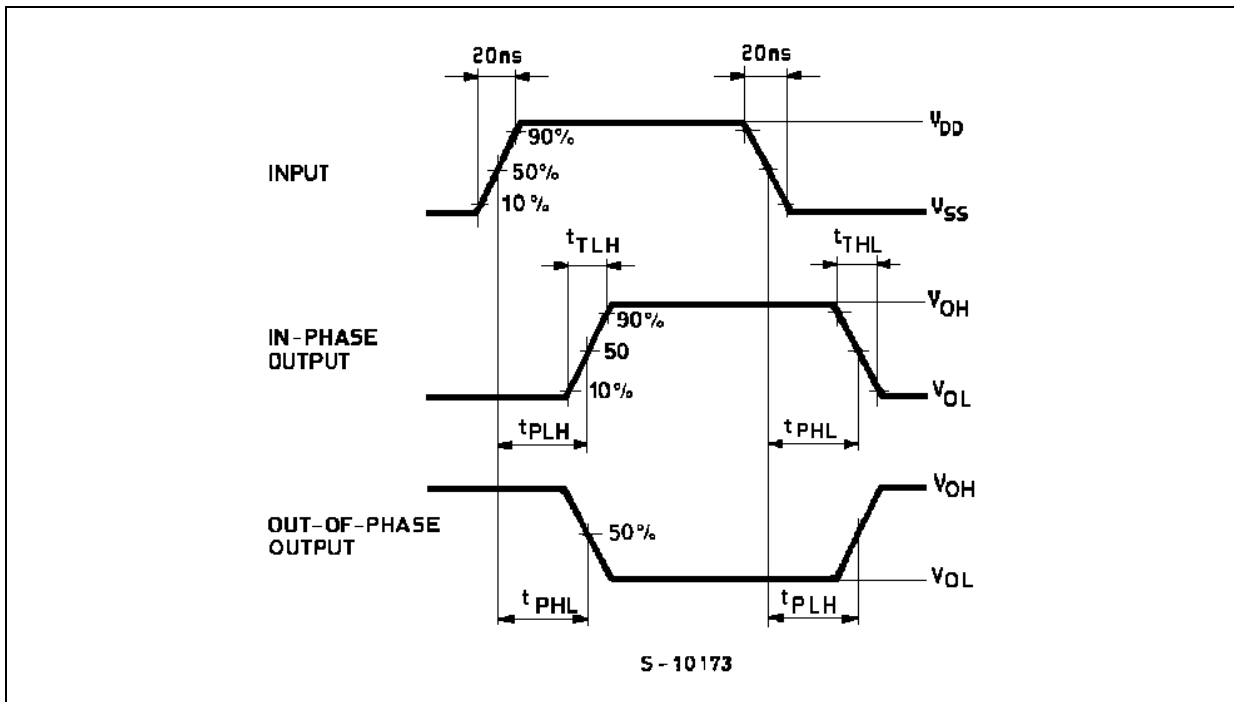
(*) Typical temperature coefficient for all V_{DD} value is 0.3 %/°C.

TEST CIRCUIT



$C_L = 50\text{pF}$ or equivalent (includes jig and probe capacitance)
 $R_L = 200\text{K}\Omega$
 $R_T = Z_{\text{OUT}}$ of pulse generator (typically 50Ω)

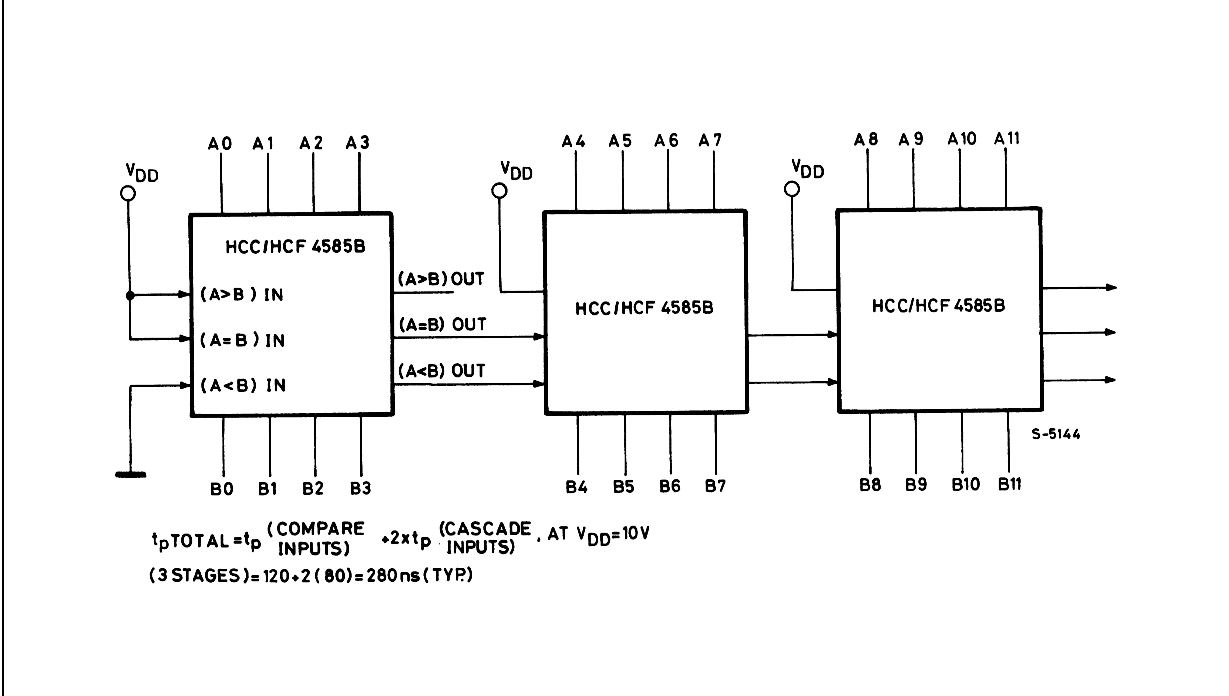
WAVEFORM : PROPAGATION DELAY TIMES ($f=1\text{MHz}$; 50% duty cycle)



HCF4585B

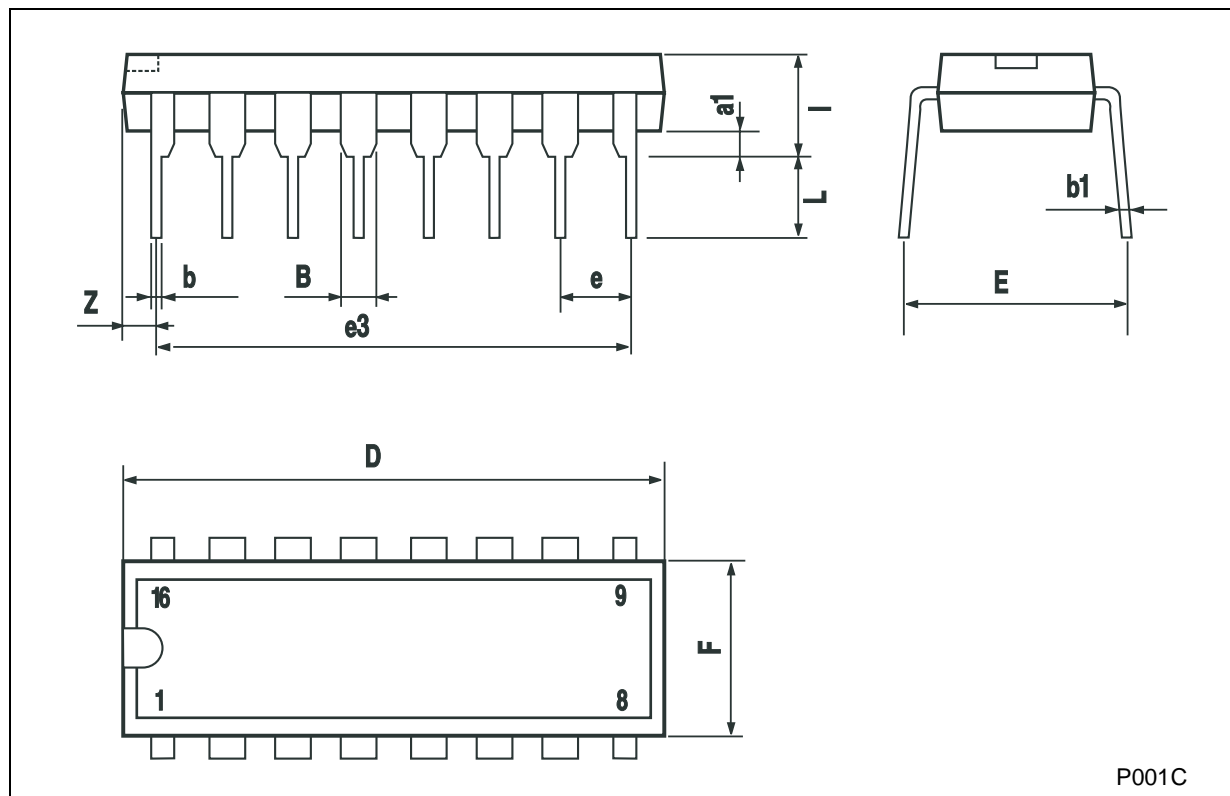
TYPICAL APPLICATION

TYPICAL SPEED CHARACTERISTICS OF A 12-BIT COMPARATOR



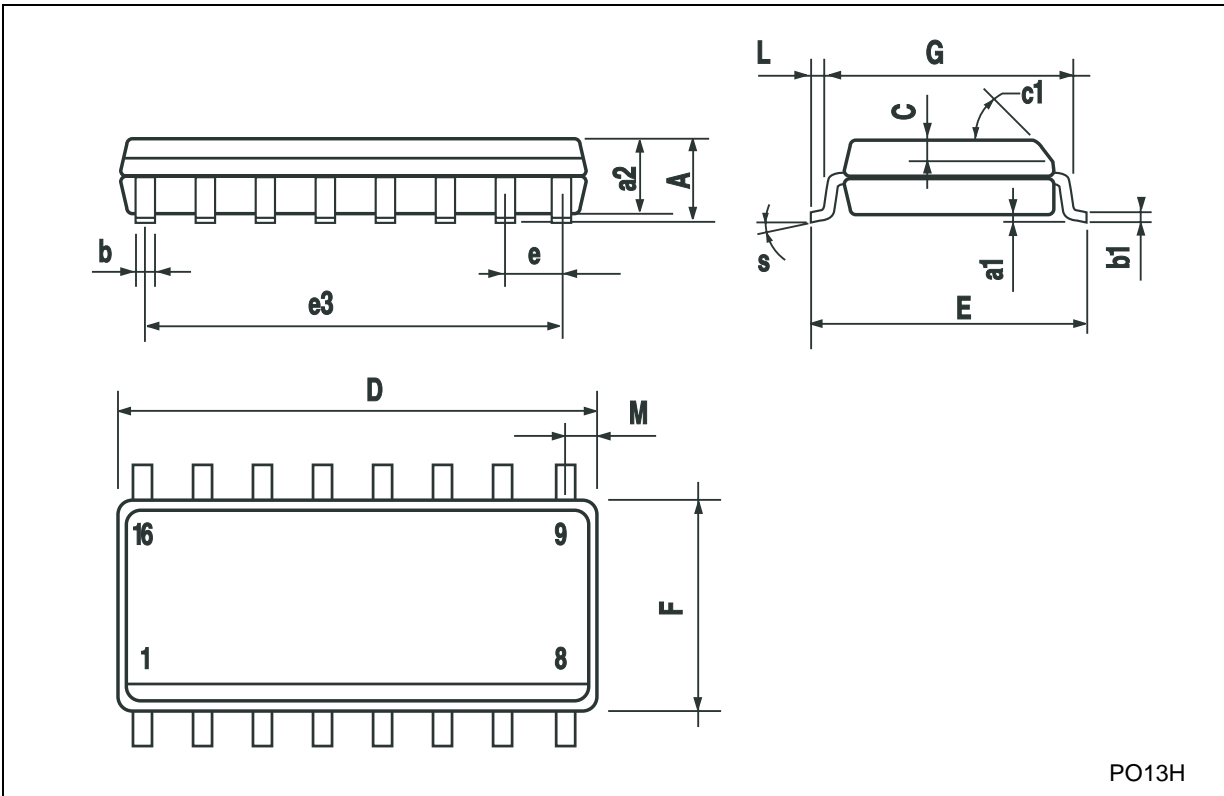
Plastic DIP-16 (0.25) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



SO-16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



PO13H

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2002 STMicroelectronics - Printed in Italy - All Rights Reserved
STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco
Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

© <http://www.st.com>





LittleDiode supplies new, hard to find or obsolete electronic components and semiconductors all over the world.

With over two million different components listed you are sure to find the part you need.

Feel free to visit us today at our online store:

LittleDiode.com

Looking forward to providing you with the best possible service.